NSN 5962-01-269-1013

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View Online at https://aerobasegroup.com/nsn/5962-01-269-1013 **Body Length:** 0.840 inches **Body Width:** Between 0.220 inches and 0.310 inches **Body Height:** 0.140 inches **Maximum Power Dissipation Rating:** 739.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius Storage Tempurature Range: -65.0/+150.0 degrees celsius **Features Provided:** Schottky and programmable and monolithic and bipolar and 3-state output **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic **Input Circuit Pattern:** 10 input **Case Outline Source And Designator:** D-2 mil-m-38510 **Terminal Surface Treatment:** Solder **Voltage Rating And Type Per Characteristic:** -0.5 volts power source and 7.0 volts power source **Time Rating Per Chacteristic:** 75.00 nanoseconds propagation delay time, low to high level output and 75.00 nanoseconds propagation delay time, high to low level output **Memory Device Type:** Rom **Test Data Document:** 96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.). **Terminal Type And Quantity:** 16 printed circuit Shelf Life:

Demilitarization:

Unit Of Measure:

Yes - demil/mli

N/a

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